



## PATENT APPLICATION

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INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub- Class
<i>jun</i>	_____	5,112,641	May 12, 1992	Harada, et al.	438	512
<i>jun</i>	_____	5,217,340	June 8, 1993	Harada, et al.	414	172
<i>jun</i>	_____	6,015,590	January 18, 2000	Suntola, et al.	427	285
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<i>jun</i>	_____	KIM, et al. Applied Physics Letters December 22, 1997, pp. 3604-3606
<i>jun</i>	_____	OTT, et al. Al <sub>3</sub> O <sub>3</sub> Thin Film Growth on Si (100) Using Binary Reaction Sequence Chemistry, (1997) 135-144
<i>jun</i>	_____	GOTO, et al. Atomic Layer Controlled Deposition of Silicon Nitride With Self-Limiting Mechanism

Examiner: *Julio F. Maldonado*Date Considered: *09/20/2002*